NEW PRODUCT

ZVNL110G

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = 25°C
100V	3.0Ω @ V_{GS} = 10V	0.6A
	4.5Ω @ V_{GS} = 5.0V	0.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features and Benefits

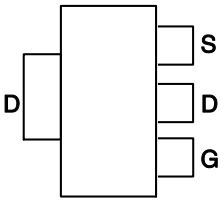
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

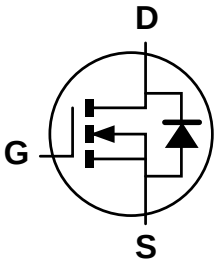
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (Approximate)

SOT223

Top View



Pin Out - Top View



Equivalent Circuit

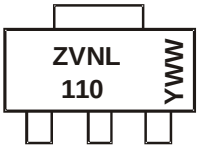
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZVNL110GTA	Standard	SOT223	1,000/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



ZVNL110 = Product Type Marking Code
YWW = Date Code Marking
Y or $\overline{Y}$ = Last Digit of Year (ex: 5= 2015)
WW or $\overline{W}W$ = Week Code (01~53)

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.6 0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle ≦ 1%)			I_{DM}	6	A
Maximum Body Diode Continuous Current (Note 6)			I_S	1.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	1.1	W
	(Note 6)		2.0	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	113	°C/W
	(Note 6)		61	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	6.6	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10 100	µA	V_{DS} = 100V, V_{GS} = 0V V_{DS} = 80V, V_{GS} = 0V, T_J = +125°C
Gate-Body Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
On-State Drain Current	$I_{D(ON)}$	750	—	—	mA	V_{DS} = 25V, V_{GS} = 5V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.75	—	1.5	V	V_{DS} = V_{GS}, I_D = 1mA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	3.0	Ω	V_{GS} = 10V, I_D = 500mA
		—	—	4.5		V_{GS} = 5.0V, I_D = 250mA
Forward Transconductance	g_{fs}	225	—	—	mS	V_{DS} = 25V, I_D = 500mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	47	75	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	23	25		
Reverse Transfer Capacitance	C_{rss}	—	6	8		
Turn-On Delay Time	$t_{D(ON)}$	—	2	7	ns	V_{DD} = 25V, V_{GS} = 10V, R_G = 6.0Ω, I_D = 1.0A
Turn-On Rise Time	t_R	—	3	12		
Turn-Off Delay Time	$t_{D(OFF)}$	—	5	15		
Turn-Off Fall Time	t_F	—	2	13		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

NEW PRODUCT

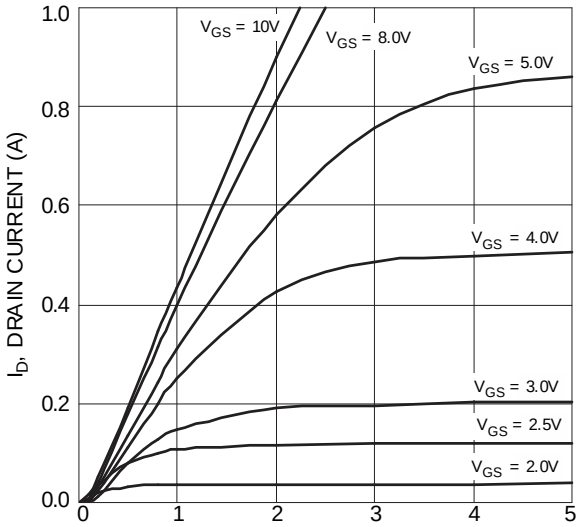


Figure 1 Typical Output Characteristics

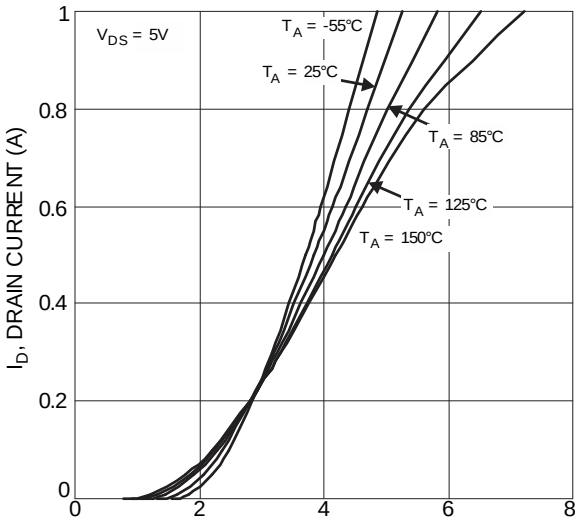


Figure 2 Typical Transfer Characteristics

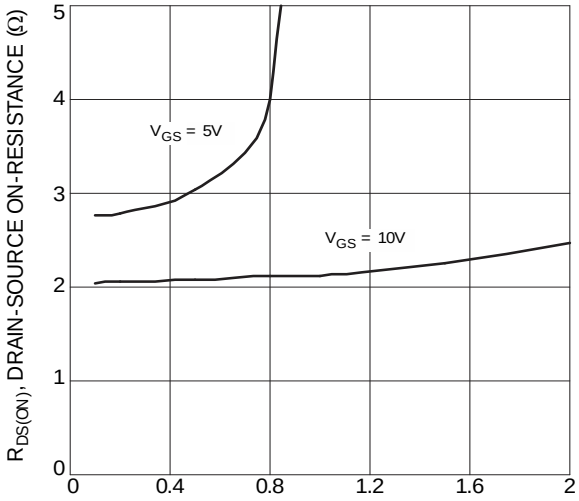


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

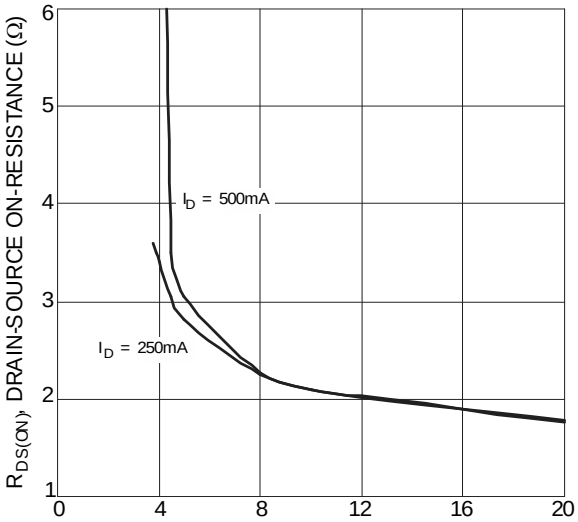


Figure 4 Typical Transfer Characteristics

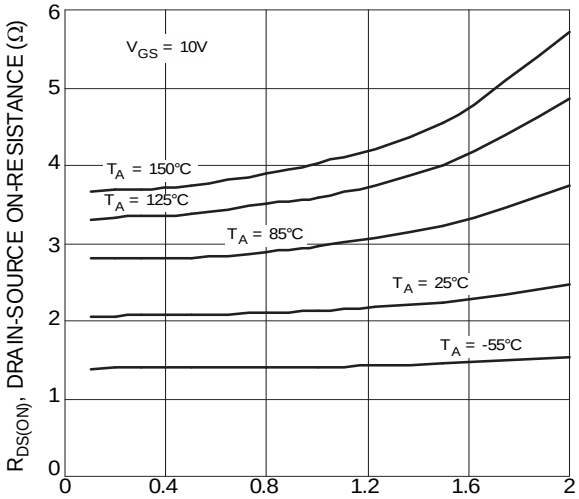


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

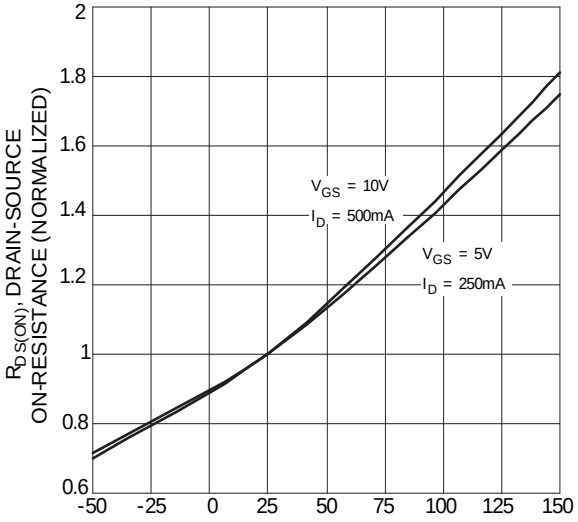


Figure 6 On-Resistance Variation with Temperature

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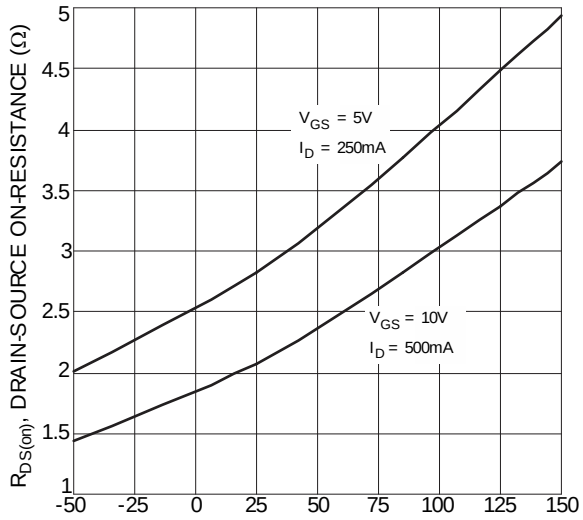

Figure 7 On-Resistance Variation with Temperature

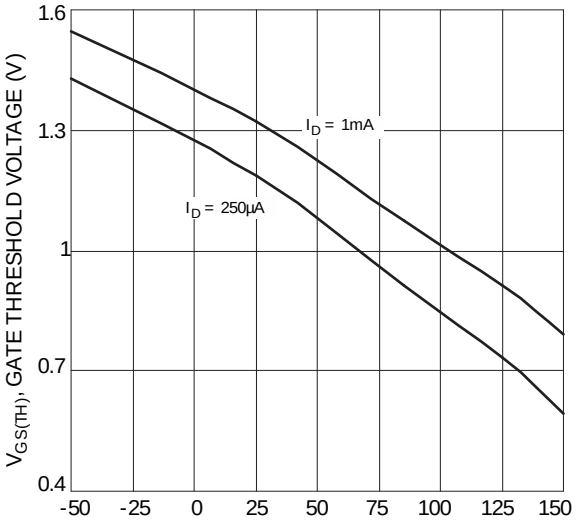

Figure 8 Gate Threshold Variation vs. Temperature

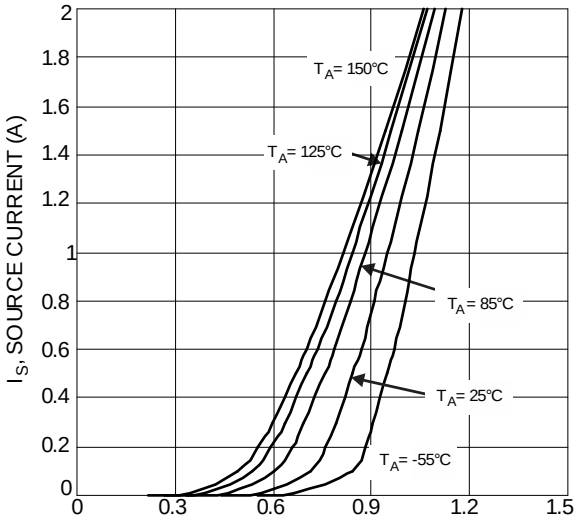

Figure 9 Diode Forward Voltage vs. Current

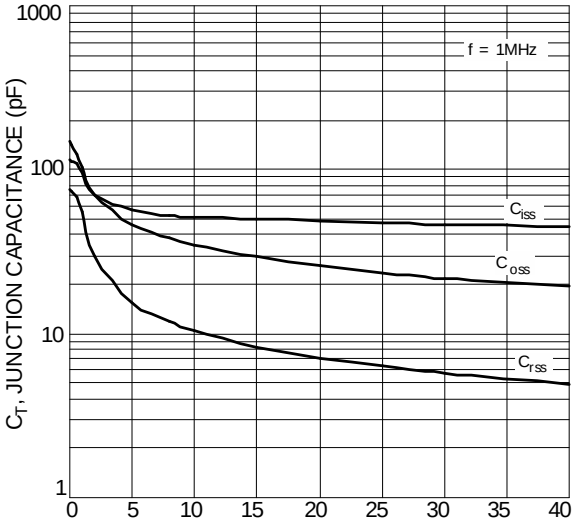

Figure 10 Typical Junction Capacitance

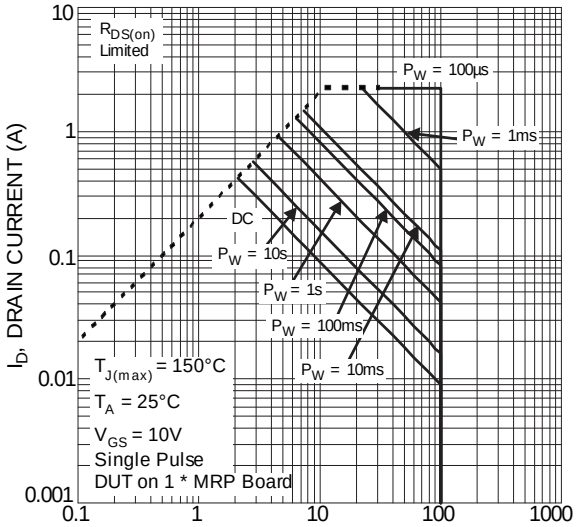

Figure 11 SOA, Safe Operation Area

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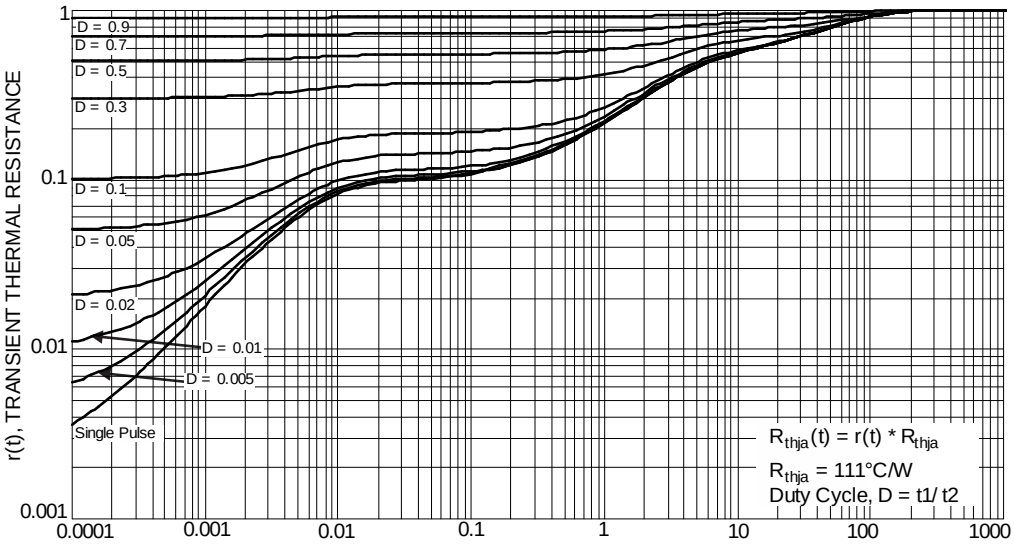
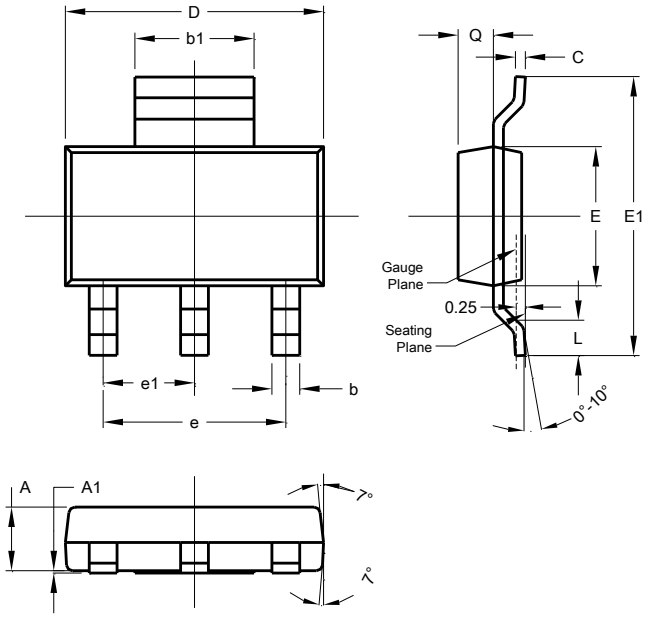


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

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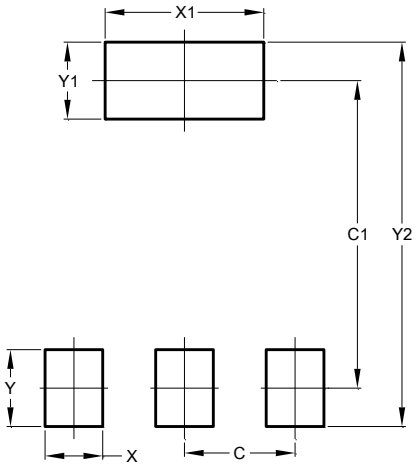
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00

Mouser Electronics

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ZVNL110GTA